International
IOR Rectifier

Preliminary Data Sheet PD - 9.1065

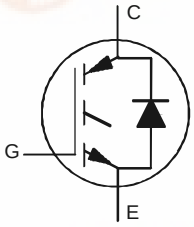
IRGP450UD2

INSULATED GATE BIPOLAR TRANSISTOR WITH ULTRAFAST SOFT RECOVERY DIODE

UltraFast CoPack IGBT

Features

- Switching-loss rating includes all "tail" losses
- HEXFRED™ soft ultrafast diodes
- Optimized for high operating frequency (over 5kHz)



n-channel

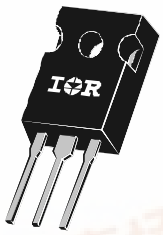
V_{CES} = 500V

$V_{CE(sat)} \leq 3.2V$

@V_{GE} = 15V, I_C = 33A

Description

Co-packaged IGBTs are a natural extension of International Rectifier's well known IGBT line. They provide the convenience of an IGBT and an ultrafast recovery diode in one package, resulting in substantial benefits to a host of high-voltage, high-current, motor control, UPS and power supply applications.



TO-247AC

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	500	V
I_C @ T_C = 25°C	Continuous Collector Current	59	A
I_C @ T_C = 100°C	Continuous Collector Current	33	
I_{CM}	Pulsed Collector Current ①	120	
I_{LM}	Clamped Inductive Load Current ②	120	
I_F @ T_C = 100°C	Diode Continuous Forward Current	29	
I_{FM}	Diode Maximum Forward Current	120	
V_{GE}	Gate-to-Emitter Voltage	± 20	V
P_D @ T_C = 25°C	Maximum Power Dissipation	200	W
P_D @ T_C = 100°C	Maximum Power Dissipation	78	
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to +150	°C
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	
	Mounting Torque, 6-32 or M3 Screw.	10 lbf•in (1.1 N•m)	

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case - IGBT	—	—	0.64	°C/W
$R_{\theta JC}$	Junction-to-Case - Diode	—	—	0.83	
$R_{\theta CS}$	Case-to-Sink, flat, greased surface	—	0.24	—	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	—	—	40	
Wt	Weight	—	6 (0.21)	—	g (oz)

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage ③	500	—	—	V	V_{GE} = 0V, I_C = 250µA
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.41	—	V/°C	V_{GE} = 0V, I_C = 1.0mA
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	—	2.1	3.2	V	I_C = 33A V_{GE} = 15V
		—	2.6	—		I_C = 59A
		—	2.1	—		I_C = 33A, T_J = 150°C
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	5.5		V_{CE} = V_{GE}, I_C = 250µA
$\Delta V_{GE(th)}/\Delta T_J$	Temperature Coeff. of Threshold Voltage	—	-10	—	mV/°C	V_{CE} = V_{GE}, I_C = 250µA
g_{fe}	Forward Transconductance ④	7.0	22	—	S	V_{CE} = 100V, I_C = 33A
I_{CES}	Zero Gate Voltage Collector Current	—	—	250	µA	V_{GE} = 0V, V_{CE} = 500V
		—	—	6500		V_{GE} = 0V, V_{CE} = 500V, T_J = 150°C
V_{FM}	Diode Forward Voltage Drop	—	1.3	1.7	V	I_C = 25A
		—	1.2	1.5		I_C = 25A, T_J = 150°C
I_{GES}	Gate-to-Emitter Leakage Current	—	—	±100	nA	V_{GE} = ±20V

Switching Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge (turn-on)	—	120	180		I_C = 33A
Q_{ge}	Gate - Emitter Charge (turn-on)	—	22	33	nC	V_{CC} = 400V
Q_{gc}	Gate - Collector Charge (turn-on)	—	41	62		
$t_{d(on)}$	Turn-On Delay Time	—	33	—		T_J = 25°C
t_r	Rise Time	—	26	—	ns	I_C = 33A, V_{CC} = 400V
$t_{d(off)}$	Turn-Off Delay Time	—	110	170		V_{GE} = 15V, R_G = 5.0Ω
t_f	Fall Time	—	91	140		Energy losses include "tail" and
E_{on}	Turn-On Switching Loss	—	0.91	—		diode reverse recovery.
E_{off}	Turn-Off Switching Loss	—	0.25	—	mJ	
E_{ts}	Total Switching Loss	—	1.2	1.7		
$t_{d(on)}$	Turn-On Delay Time	—	37	—		T_J = 150°C,
t_r	Rise Time	—	29	—	ns	I_C = 33A, V_{CC} = 400V
$t_{d(off)}$	Turn-Off Delay Time	—	160	—		V_{GE} = 15V, R_G = 5.0Ω
t_f	Fall Time	—	110	—		Energy losses include "tail" and
E_{ts}	Total Switching Loss	—	1.8	—	mJ	diode reverse recovery.
L_E	Internal Emitter Inductance	—	13	—	nH	Measured 5mm from package
C_{ies}	Input Capacitance	—	2700	—		V_{GE} = 0V
C_{oes}	Output Capacitance	—	280	—	pF	V_{CC} = 30V
C_{res}	Reverse Transfer Capacitance	—	34	—		f = 1.0MHz
t_{rr}	Diode Reverse Recovery Time	—	50	75	ns	T_J = 25°C
		—	105	160		T_J = 125°C I_F = 25A
I_{rr}	Diode Peak Reverse Recovery Current	—	4.5	10	A	T_J = 25°C
		—	8.0	15		T_J = 125°C V_R = 200V
Q_{rr}	Diode Reverse Recovery Charge	—	112	375	nC	T_J = 25°C
		—	420	1200		T_J = 125°C di/dt = 200A/µs
$di_{(rec)M}/dt$	Diode Peak Rate of Fall of Recovery	—	250	—	A/µs	T_J = 25°C
	During t_b	—	160	—		T_J = 125°C

Notes: ① Repetitive rating; V_{GE}=20V, pulse width limited by max. junction temperature. (See fig. 20)

② V_{CC}=80%(V_{CES}), V_{GE}=20V, L=10µH, R_G= 5.0Ω, (See fig. 19)

③ Pulse width ≤ 80µs; duty factor ≤ 0.1%.

④ Pulse width 5.0µs, single shot.

Refer to Section D - page D-13 for Package Outline 3 - JEDEC Outline TO-247AC